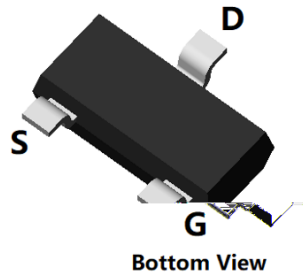
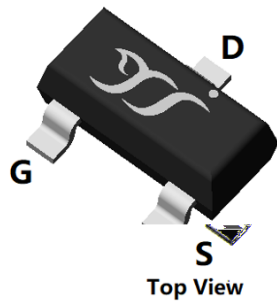
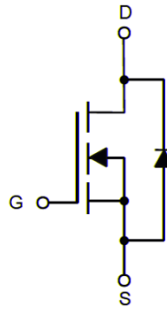


## N-Channel Enhancement Mode Field Effect Transistor



**SOT-23**



### Product Summary

• $V_{DS}$	30V
• $I_D$	5.6A
• $R_{DS(ON)}$ ( at $V_{GS}=10V$ )	<25mohm
• $R_{DS(ON)}$ ( at $V_{GS}=4.5V$ )	<31mohm
• $R_{DS(ON)}$ ( at $V_{GS}=2.5V$ )	<45mohm

### General Description

- Trench Power LV MOSFET technology
- High density cell design for low  $R_{DS(ON)}$
- High Speed switching
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

### Applications

- Battery protection
- Load switch
- Power management

### ■ Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	$V_{DS}$	30	V
Gate-source Voltage	$V_{GS}$	$\pm 12$	V
Drain Current	$I_D$	$T_A=25^\circ\text{C}$	5.6
		$T_A=70^\circ\text{C}$	4.5
Pulsed Drain Current <sup>A</sup>	$I_{DM}$	23	A
Total Power Dissipation	$P_D$	$T_A=25^\circ\text{C}$	1.2
		$T_A=70^\circ\text{C}$	0.8
Thermal Resistance Junction-to-Ambient <sup>B</sup>	$R_{\theta JA}$	104	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~+150	$^\circ\text{C}$

### ■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJL3400A	F2	3400.	3000	30000	120000	7" reel



# YJL3400A

## ■ Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	30			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	μA
Gate-Body Leakage Current	I <sub>GSS1</sub>	V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V			±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.65	0.9	1.5	V
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =5.6A		20	25	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A		23	31	
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =3A		27	45	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =5.6A, V <sub>GS</sub> =0V			1.2	V
<b>Dynamic Parameters</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHZ		630		pF
Output Capacitance	C <sub>oss</sub>			55		
Reverse Transfer Capacitance	C <sub>rss</sub>			71		
<b>Switching Parameters</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, I <sub>D</sub> =5.6A		17.25		nC
Gate-Source Charge	Q <sub>gs</sub>			2.1		
Gate-Drain Charge	Q <sub>gd</sub>			2		
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> =5.6A, di/dt=100A/us		1.1		ns
Reverse Recovery Time	t <sub>rr</sub>			13.1		
Turn-on Delay Time	t <sub>D(on)</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, I <sub>D</sub> =5.6A R <sub>GEN</sub> =3Ω		4.4		ns
Turn-on Rise Time	t <sub>r</sub>			28.2		
Turn-off Delay Time	t <sub>D(off)</sub>			16.2		
Turn-off fall Time	t <sub>f</sub>			26		

A. Pulse Test: Pulse Width ≤ 300us, Duty cycle ≤ 2%.

B. R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>θJC</sub> is guaranteed by design, while R<sub>θJA</sub> is determined by the board design. The maximum rating presented here is based on mounting on a 1 in 2 pad of 2oz copper.



## ■ Typical Performance Characteristics

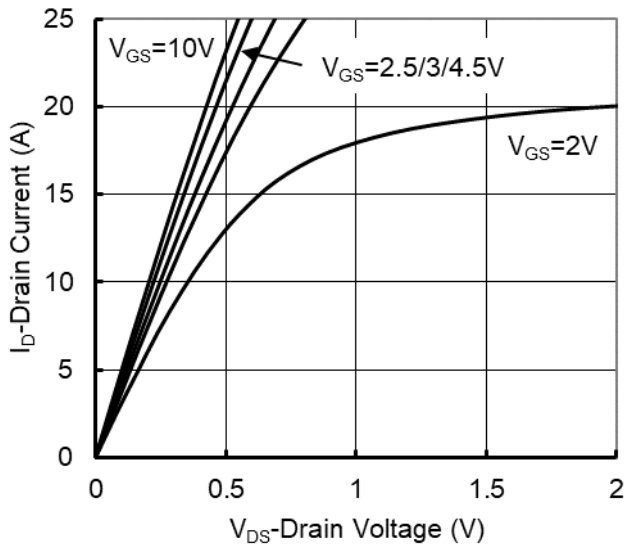


Figure1. Output Characteristics

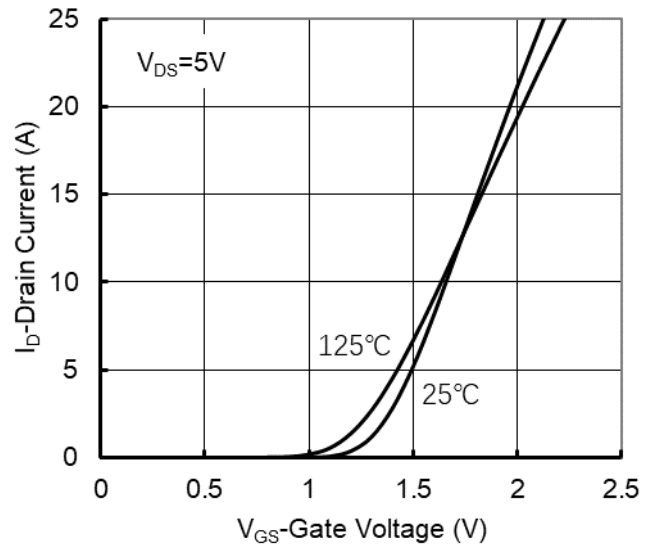


Figure2. Transfer Characteristics

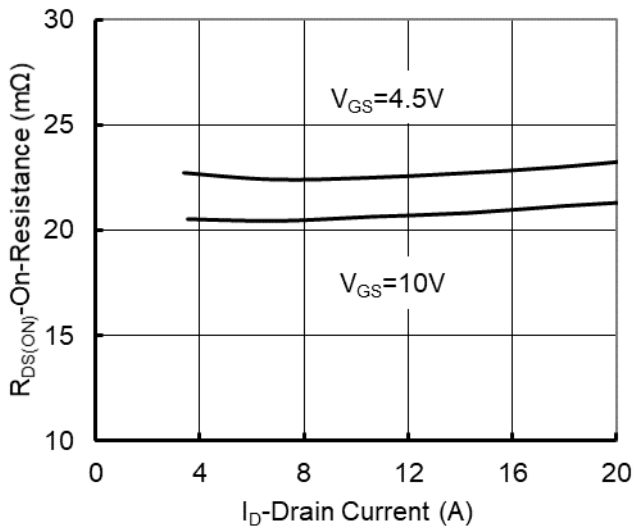


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

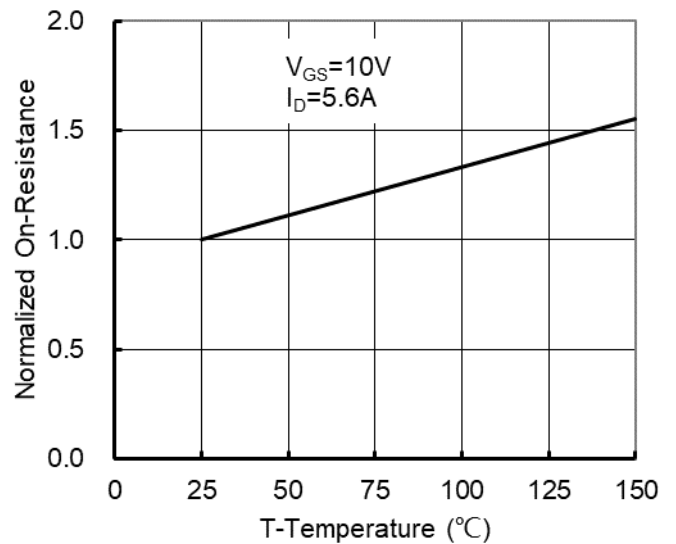


Figure 4: On-Resistance vs. Junction Temperature

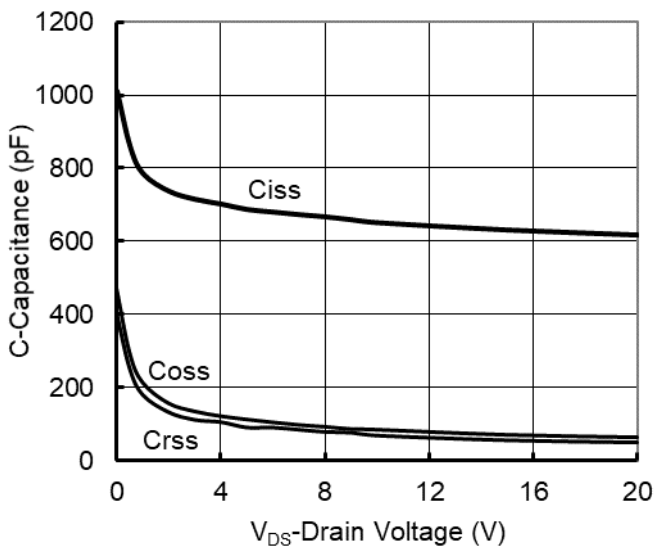


Figure5. Capacitance Characteristics

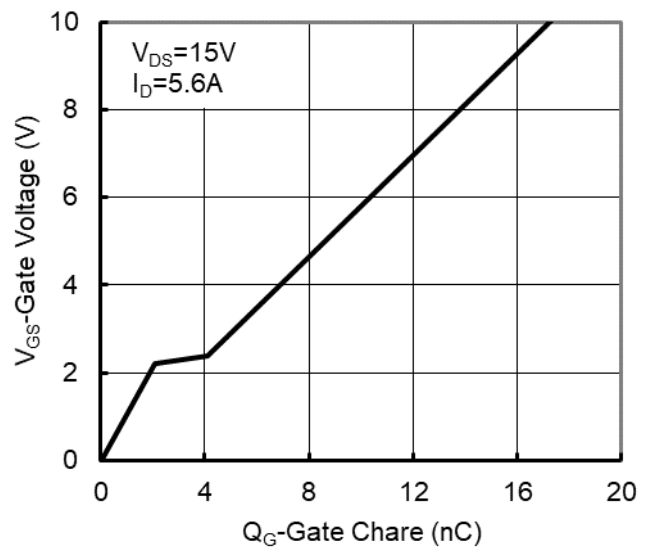


Figure6. Gate Charge



# YJL3400A

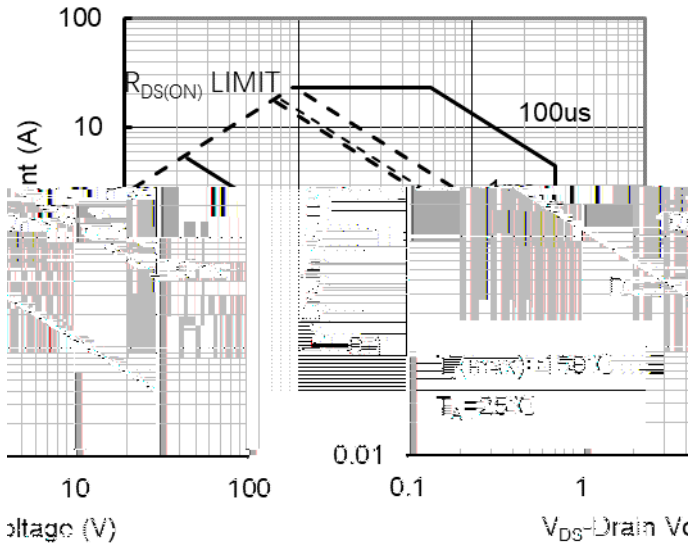


Figure7. Safe Operation Area

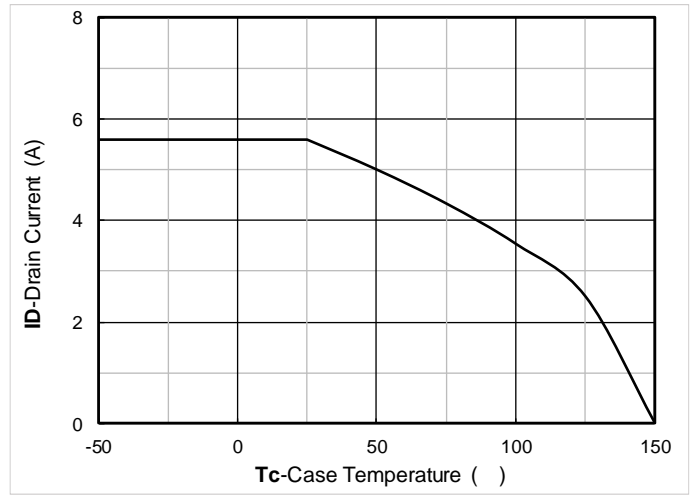


Figure8. Current dissipation

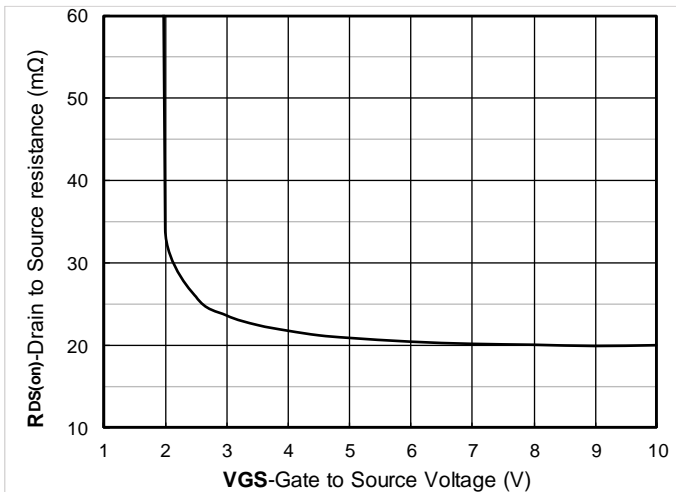


Figure 9. On-Resistance vs Gate to Source Voltage

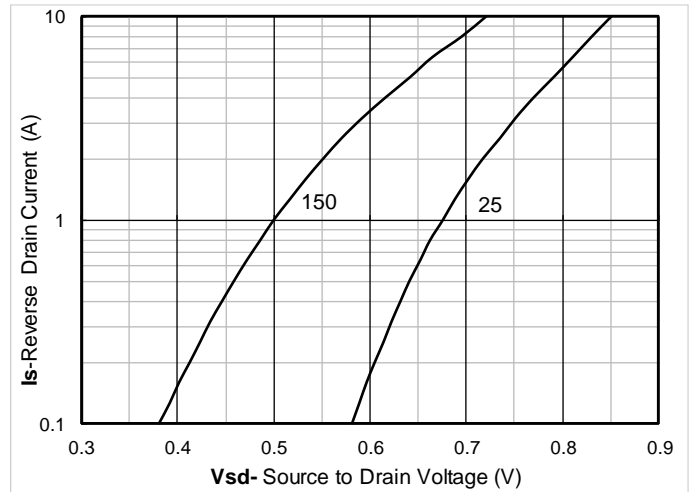


Figure 10. Forward characteristics of reverse diode

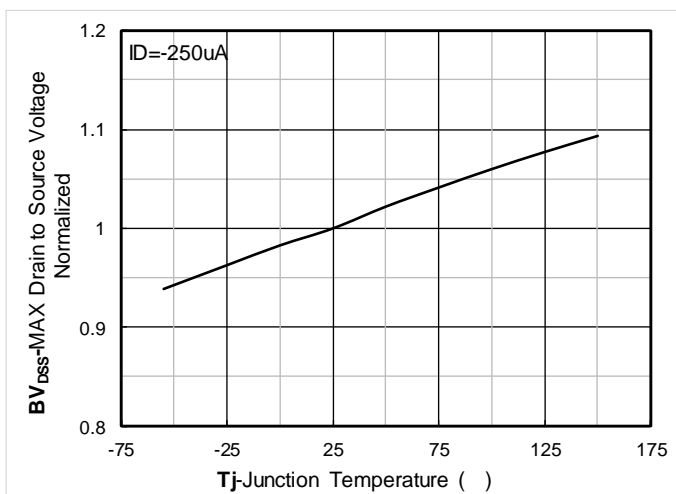


Figure 11. Normalized breakdown voltage

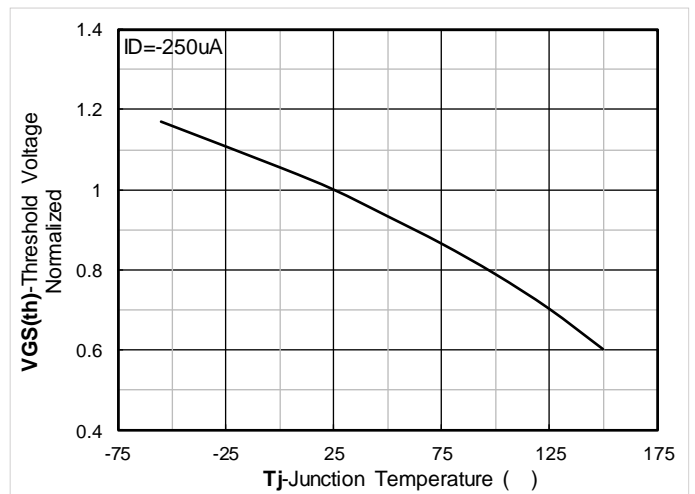


Figure 12. Normalized Threshold voltage



# YJL3400A

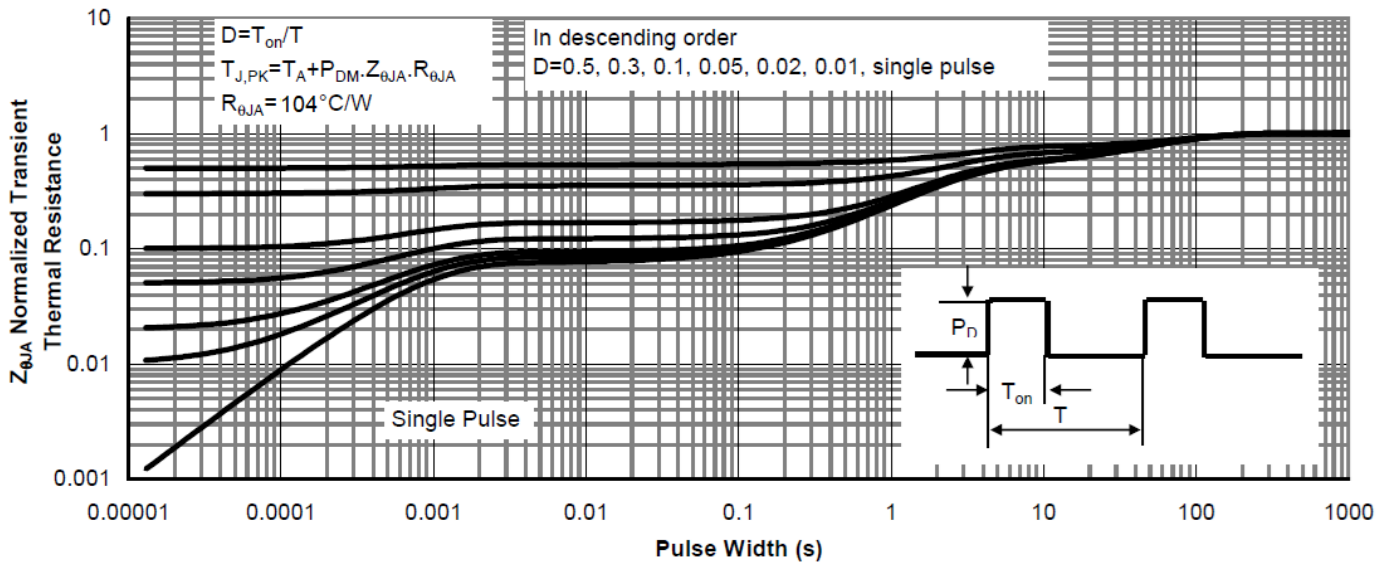
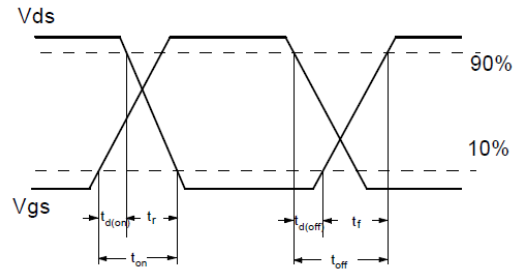
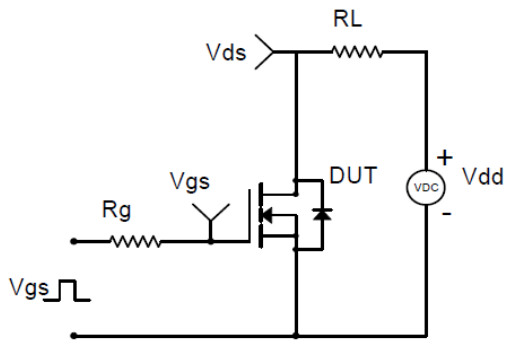
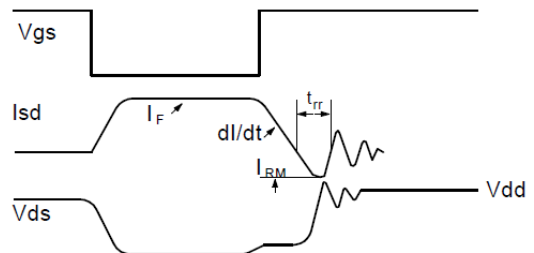
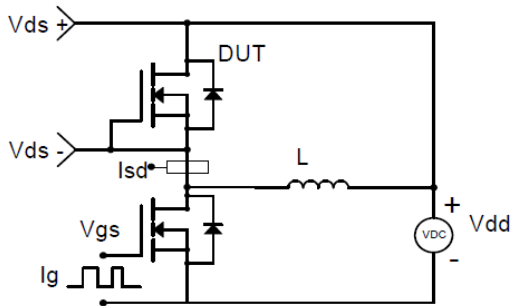


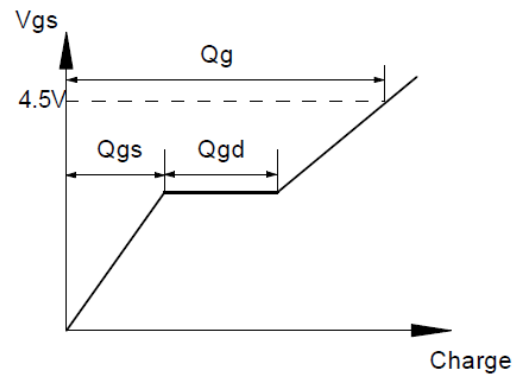
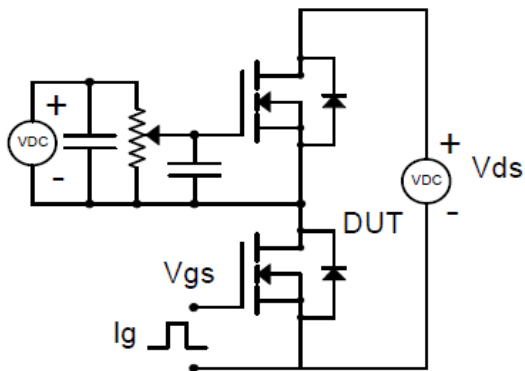
Figure13. Normalized Maximum Transient Thermal Impedance



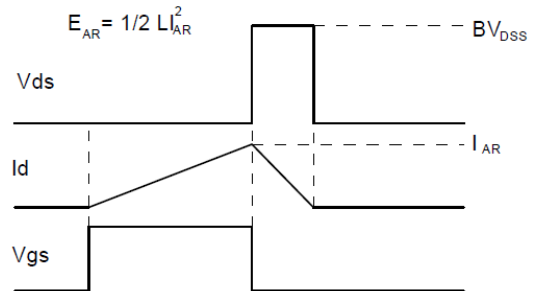
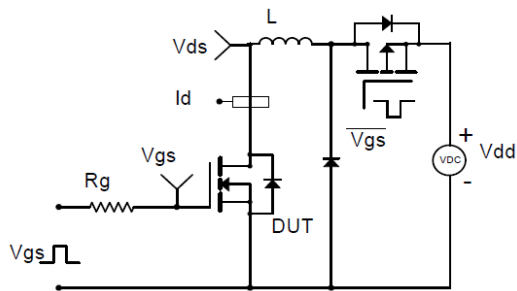
**Resistive Switching Test Circuit & Waveforms**



**Diode Recovery Test Circuit & Waveforms**



**Gate Charge Test Circuit & Waveform**

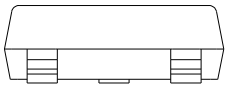
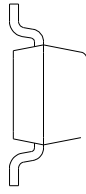
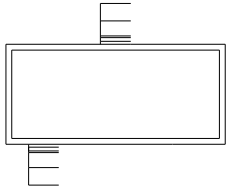


**Unclamped Inductive Switching (UIS) Test Circuit & Waveforms**



# YJL3400A

## ■ SOT-23 Package information



UNIT: mm



## YJL3400A

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